

Amendments to the Claims:

1. (currently amended) A process for reducing the concentration of water and optionally at least one impurity, from a cyclosiloxane precursor, comprising wherein said process is selected from the group consisting of:

(1) contacting the cyclosiloxane precursor with an adsorbent bed material, so as to remove therefrom at least a portion of the water, and optionally the at least one other impurity, to produce a cyclosiloxane precursor having a reduced level of water and optionally the at least one impurity; and removing the purified cyclosiloxane precursor from the adsorbent bed material; and

(2) distilling a starting mixture comprising at least water and at least one [SiO]_n cyclosiloxane CVD chemical vapor deposition precursor, wherein n is from 2 to 8, in the presence of an azeotropic component, so as to form an azeotropic mixture with the water contained in said starting mixture; in order to produce (A) a distillate fraction comprising water and the azeotropic component and (B) a balance fraction comprising a purified cyclosiloxane precursor, whereby said balance fraction (B) is substantially reduced in water relative to said starting mixture; and

(3) a combination of 1 and 2.

2. (original) The process according to claim 1, wherein said impurity is selected from the group consisting of acidic and basic impurities.

3. (original) The process according to claim 1, wherein said impurity is acidic.

4. (original) The process according to claim 1, wherein said impurity is basic.

5. (original) The process according to claim 1, wherein said cyclosiloxane precursor comprises the formula [RR'Si-O]_n, wherein each of R and R' is same or different and independently selected from the group consisting of hydrogen, hydroxyl, C₁-C₈ alkyl, C₁-C₈ alkoxy, C₁-C₈ alkene, C₁-C₈ alkyne, and C₁-C₈ carboxyl; and n is from 2 to 8.

6. (original) The process according to claim 1, wherein the cyclosiloxane precursor is selected from the group consisting of polyhedral oligomeric silsesquioxanes (POSS), octamethylcyclotetrasiloxane (OMCTS), hexamethylcyclotetrasiloxane (HMCTS), tetramethylcyclotetrasiloxane (TMCTS), and mixtures thereof.

7. (original) The process according to claim 1, wherein the cyclosiloxane precursor is 1,3,5,7-tetramethylcyclotetrasiloxane.

Claim 8 is canceled.

9. (original) The process according to claim 1, wherein said adsorbent bed material is selected from the group consisting of: silica gel, molecular sieves, aluminum oxide, and carbon.

10. (currently amended) The process according to claim 1, wherein said adsorbent bed material drying agent is selected from the group consisting of: calcium oxide, calcium chloride, sodium sulfate, magnesium perchlorate, phosphorus pentoxide, silicide, metals, and metal hydrides, such as calcium hydride.

11. (currently amended) The process according to claim 1, wherein the adsorbent bed material drying agent is calcium oxide.

12. (currently amended) The process according to claim 1, wherein the drying agent adsorbent bed material is calcium hydride.

13. (currently amended) The process according to claim 1, wherein the adsorbent bed material further comprises a combination of adsorbents a second adsorbent or a drying agent.

14. (currently amended) The process according to claim 1, wherein the adsorbent bed material further comprises a second adsorbent bed material drying agent further comprises a second drying agent or an adsorbent.

15. (currently amended) The process according to claim 1, wherein said purified cyclosiloxane precursor is removed from said adsorbent bed material and/or drying agent by distillation.

16. (currently amended) The process according to claim 1, wherein said purified cyclosiloxane precursor is removed from said adsorbent bed material and/or drying agent by decantation.

17. (currently amended) The process according to claim 1, wherein said purified cyclosiloxane precursor is removed from said adsorbent bed material and/or drying agent by pump.

18. (currently amended) The process according to claim 2, wherein the level of the at least one impurity in the purified cyclosiloxane precursor is reduced to ~~a level of~~ less than < 0.001%.

19. (currently amended) The process according to claim 2, wherein the level of the at least one impurity in the purified cyclosiloxane precursor is reduced to ~~a level of~~ less than < 0.00001%.

20. (currently amended) The process according to claim 2, wherein the level of water in the purified cyclosiloxane precursor is reduced to ~~a level of~~ less than < 0.001%.

21. (currently amended) The process according to claim 2, wherein the level of water in the purified cyclosiloxane precursor is reduced to ~~a level of~~ less than < 0.00001%.

Claims 22- 46 (canceled).